

SKM 100GB12T4



SEMITRANS® 2

IGBT4 Modules

SKM 100GB12T4

Features

- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. generation CAL diode (CAL4)

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

Remarks

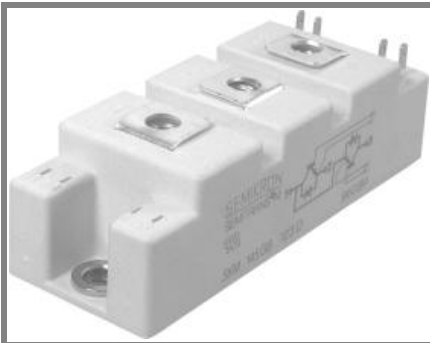
- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j \leq 150^\circ$



GB

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200		V
I_C	$T_j = 175^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	160	A
		$T_{case} = 80^\circ\text{C}$	125	A
I_{CRM}	$I_{CRM} = 3 \times I_{CNOM}$	300		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 800\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		μs
Inverse Diode				
I_F	$T_j = 175^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	120	A
		$T_{case} = 80^\circ\text{C}$	90	A
I_{FRM}	$I_{FRM} = 3 \times I_{FNOM}$	300		A
I_{FSM}	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 150^\circ\text{C}$	550	A
Module				
$I_{t(RMS)}$		200		A
T_{vj}		-40 ... +175		$^\circ\text{C}$
T_{stg}		-40 ... +125		$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000		V

Characteristics		$T_c = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 4\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = V, V_{CE} = V_{CES}, T_j = 25^\circ\text{C}$				mA
V_{CE0}		$T_j = 25^\circ\text{C}$	0,8	0,9	V
		$T_j = 150^\circ\text{C}$	0,7	0,8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	10	11	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	15	16	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 100\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,8	2	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	2,2	2,4	V
C_{res}	$V_{CE} = 25, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		6,2		nF
C_{oes}			0,41		nF
C_{res}			0,35		nF
Q_G	$V_{GE} = -8\text{V}/+15\text{V}$		570		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		7,5		Ω
$t_{d(on)}$	$R_{Gon} = 1\ \Omega$ $di/dt = 1800\text{ A}/\mu\text{s}$	$V_{CC} = 600\text{V}$ $I_C = 100\text{A}$	165		ns
t_r			47		ns
E_{on}	$R_{Goff} = 1\ \Omega$ $di/dt = 1130\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$ $V_{GE} = \pm 15\text{V}$	15		mJ
$t_{d(off)}$			400		ns
t_f			75		ns
E_{off}			10,2		mJ
$R_{th(j-c)}$	per IGBT			0,27	K/W



SEMITRANS® 2

IGBT4 Modules

SKM 100GB12T4

Features

- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. generation CAL diode (CAL4)

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j \leq 150^\circ$

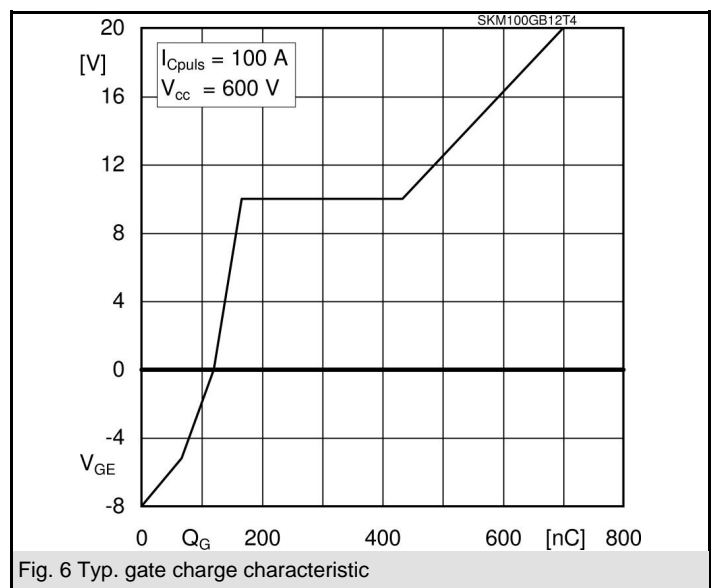
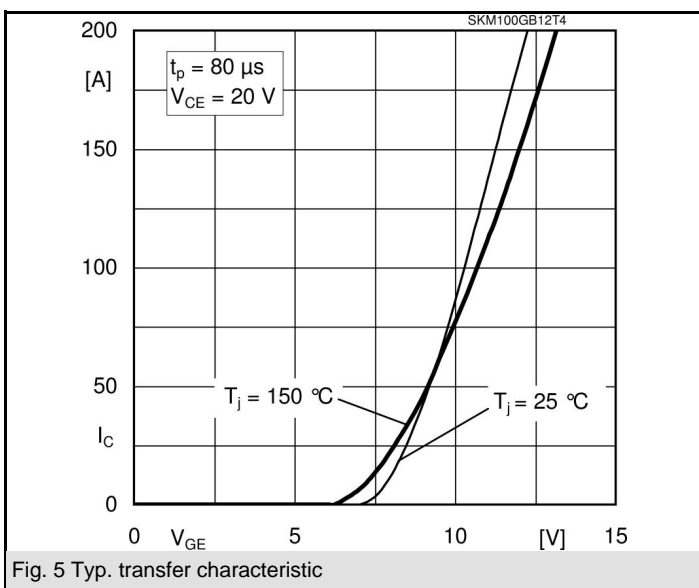
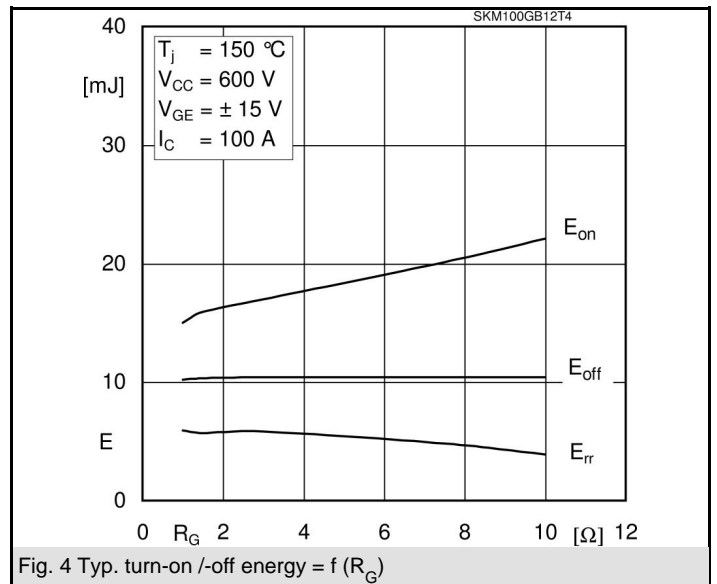
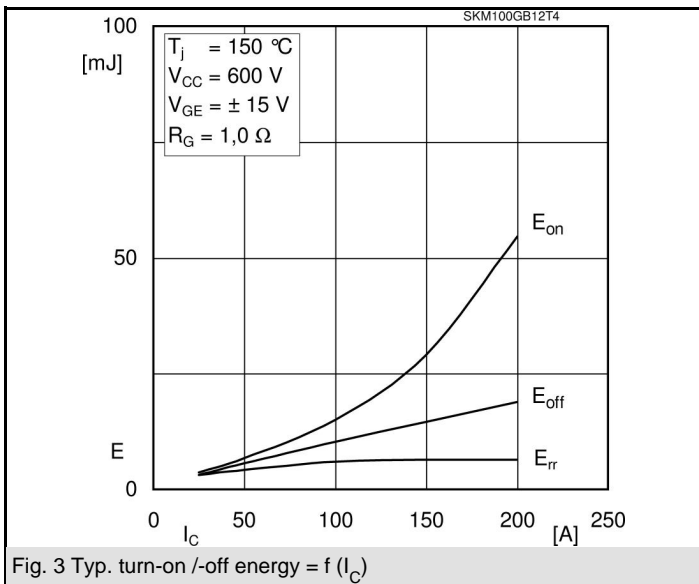
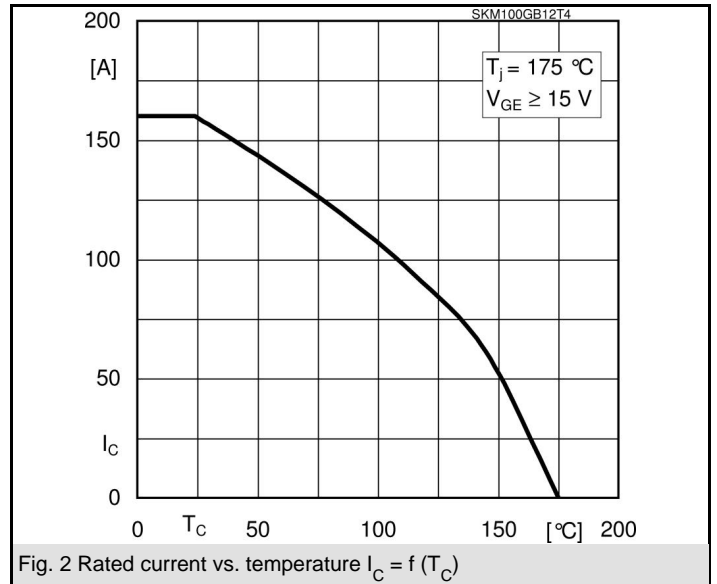
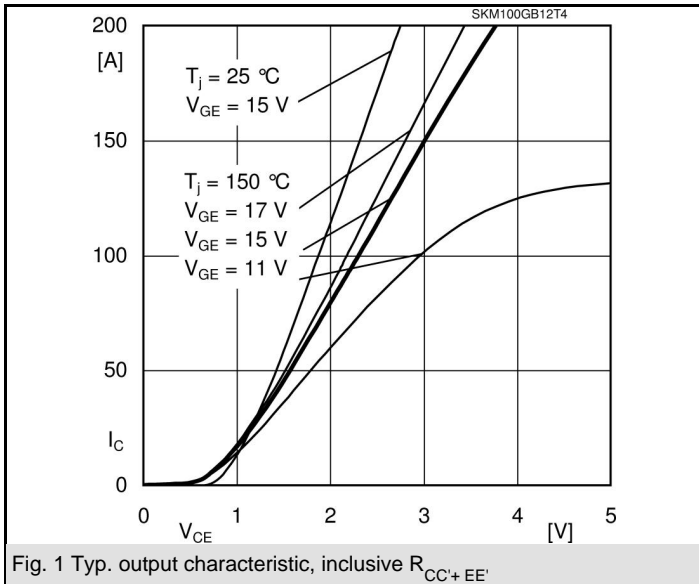


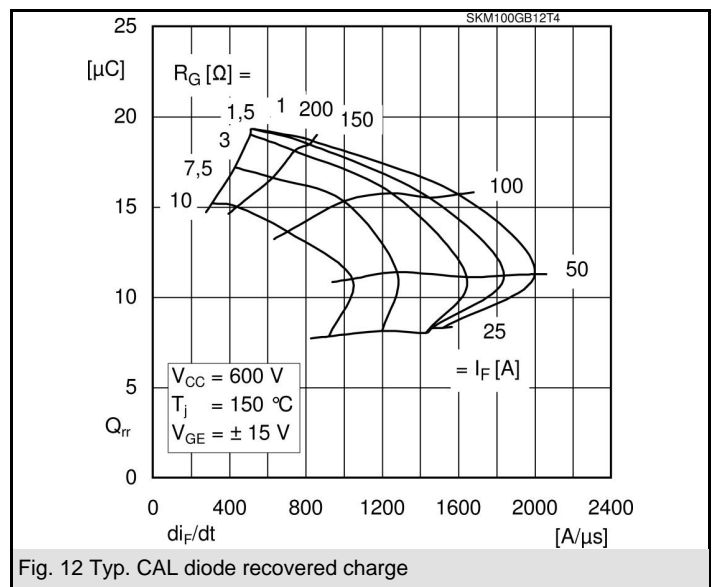
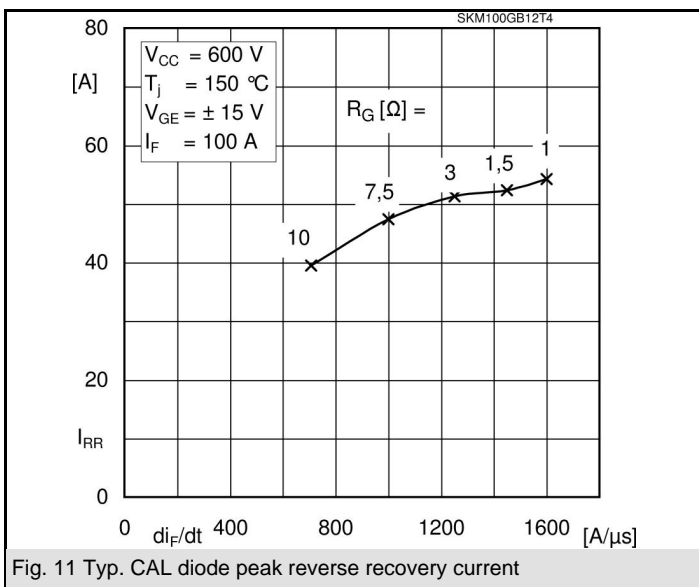
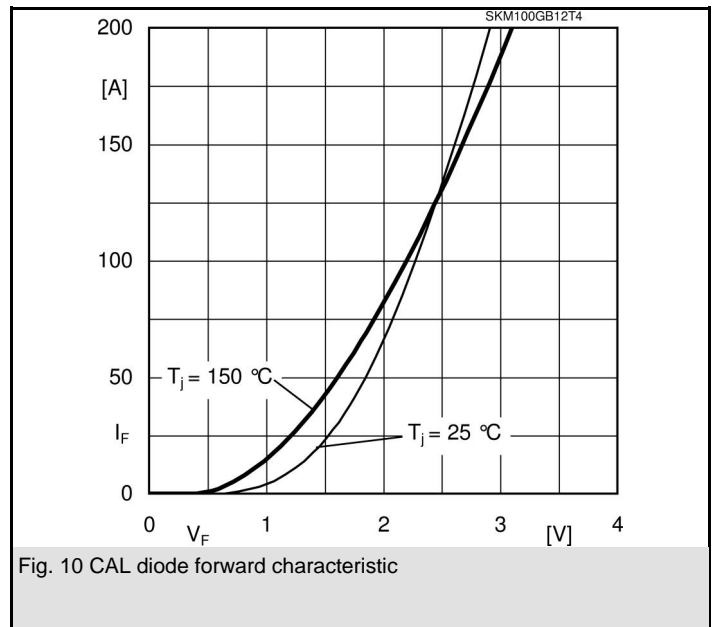
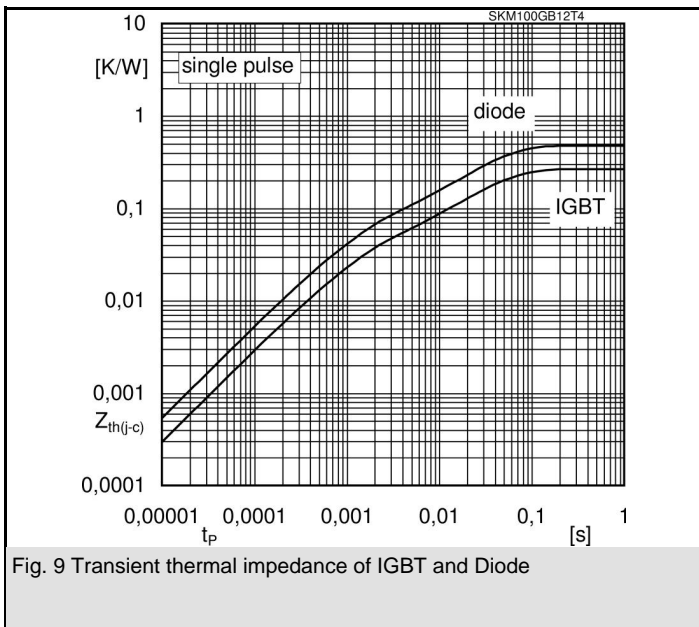
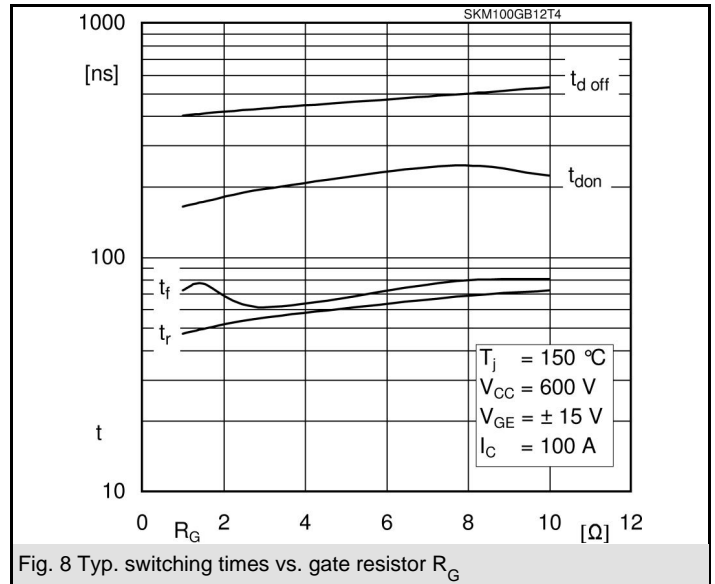
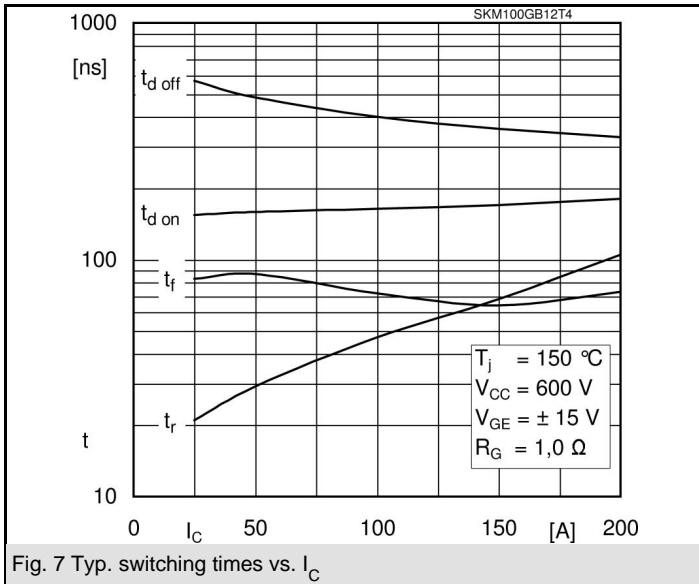
GB

Characteristics			min.	typ.	max.	Units
Symbol	Conditions					
Inverse Diode						
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$		2,2	2,5	V
		$T_j = 150^\circ\text{C}_{chiplev.}$		2,1	2,45	V
V_{F0}		$T_j = 25^\circ\text{C}$		1,3	1,5	V
		$T_j = 150^\circ\text{C}$		0,9	1,1	V
r_F		$T_j = 25^\circ\text{C}$		9	11	mΩ
		$T_j = 150^\circ\text{C}$		12	13,5	mΩ
I_{RRM}	$I_F = 100 \text{ A}$	$T_j = 150^\circ\text{C}$		54		A
Q_{rr}	$di/dt = 1600 \text{ A}/\mu\text{s}$			15,7		μC
E_{rr}	$V_{GE} \leq -8\text{V}$			5,9		mJ
$R_{th(j-c)}$	per diode				0,48	K/W
Freewheeling Diode						
$V_F = V_{EC}$	$I_{Fnom} = \text{A}; V_{GE} = \text{V}$	$T_j = ^\circ\text{C}_{chiplev.}$				V
V_{F0}		$T_j = ^\circ\text{C}$				V
r_F		$T_j = ^\circ\text{C}$				V
I_{RRM}	$I_F = \text{A}$	$T_j = ^\circ\text{C}$				A
Q_{rr}						μC
E_{rr}						mJ
	per diode					K/W
Module						
L_{CE}				20	30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$			0,75	mΩ
		$T_{case} = 125^\circ\text{C}$			1	mΩ
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6			3	5	Nm
M_t	to terminals M5			2,5	5	Nm
w					160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



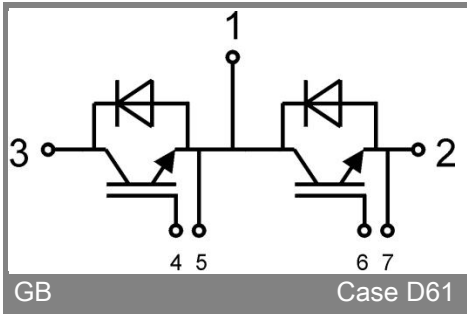
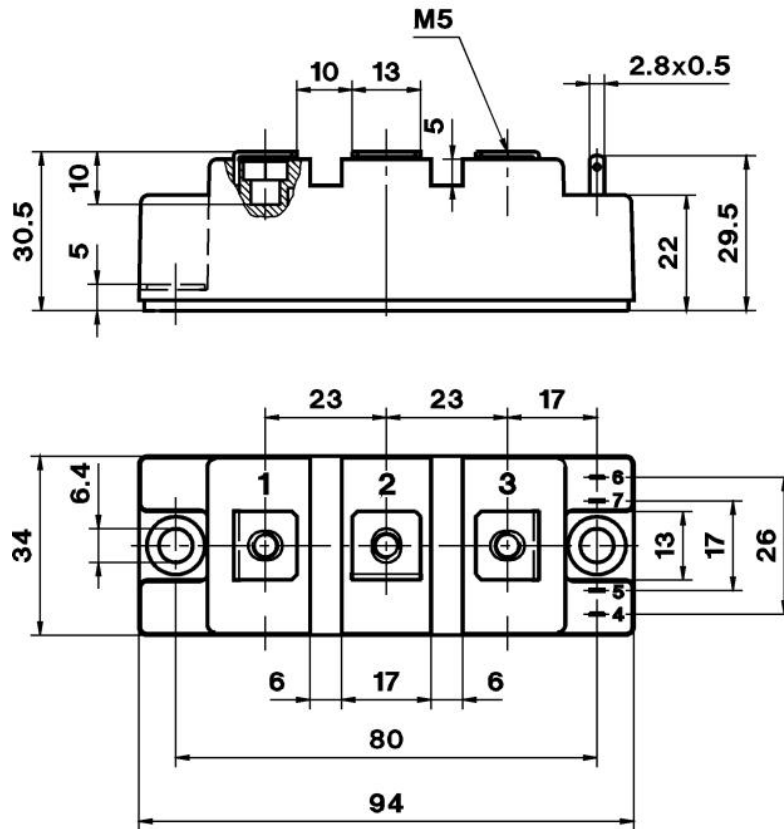


SKM 100GB12T4

UL recognized file

CASED61

no. E 63 532



GB

Case D61